



innovative clocking systems, always worthy of ISSCC/JSSC publications and for a while Alpha processors were leading the industry in terms of clock performance. I had huge shoes to fill. Obviously, I was overwhelmed, confused and highly confident that I would drag the entire project down.

This book is devoted to the subject of adaptive techniques for smart analog and mixed signal design whereby fully functional first-pass silicon is achievable. To our knowledge, this is the first book devoted to this subject. The techniques described should lead to quantum improvement in design productivity of complex analog and mixed signal systems while significantly cutting the spiraling costs of product development in emerging nanometer technologies.

A modern take on microelectronic device engineering Microelectronics is a 50-year-old engineering discipline still undergoing rapid evolution and societal adoption. Integrated Microelectronic Devices: Physics and Modeling fills the need for a rigorous description of semiconductor device physics that is relevant to modern nanoelectronics. The central goal is to present the fundamentals of semiconductor device operation with relevance to modern integrated microelectronics. Emphasis is devoted to frequency response, layout, geometrical effects, parasitic issues and modeling in integrated microelectronics devices (transistors and diodes). In addition to this focus, the concepts learned here are highly applicable in other device contexts. This text is suitable for a one-semester junior or senior-level course by selecting the front sections of selected chapters (e.g. 1-9). It can also be used in a two-semester senior-level or a graduate-level course by taking advantage of the more advanced sections.

The book provides a comprehensive overview of electromigration and its effects on the reliability of electronic circuits. It introduces the physical process of electromigration, which gives the reader the requisite understanding and knowledge for adopting appropriate counter measures. A comprehensive set of options is presented for modifying the present IC design methodology to prevent electromigration. Finally, the authors show how specific effects can be exploited in present and future technologies to reduce electromigration's negative impact on circuit reliability.

Fundamentals of Semiconductor Devices provides a realistic and practical treatment of modern semiconductor devices. A solid understanding of the physical processes responsible for the electronic properties of semiconductor materials and devices is emphasized. With this emphasis, the reader will appreciate the underlying physics behind the equations derived and their range of applicability. The author's clear writing style, comprehensive coverage of the core material, and attention to current topics are key strengths of this book.

Everything FPGA designers need to know about FPGAs and VLSI Digital designs once built in custom silicon are increasingly implemented in field programmable gate arrays (FPGAs). Effective FPGA system design requires a strong understanding of VLSI issues and constraints, and an understanding of the latest FPGA-specific techniques. In this book, Princeton University's Wayne Wolf covers everything FPGA designers need to know about all these topics: both the "how" and the "why." Wolf begins by introducing the essentials of VLSI: fabrication, circuits, interconnects, combinational and sequential logic design, system architectures, and more. Next, he demonstrates how to reflect this VLSI knowledge in a state-of-the-art design methodology that leverages FPGA's most valuable characteristics while mitigating its limitations.

Coverage includes: How VLSI characteristics affect FPGAs and FPGA-based logic design How classical logic design techniques relate to FPGA-based logic design Understanding FPGA fabrics: the basic programmable structures of FPGAs Specifying and optimizing logic to address size, speed, and power consumption Verilog, VHDL, and software tools for optimizing logic and designs The structure of large digital systems, including register-transfer design methodology Building large-scale platform and multi-FPGA systems A start-to-finish DSP case study addressing a wide range of design problems PRENTICE HALL Professional Technical Reference Upper Saddle River, NJ 07458 www.phptr.com ISBN: 0-13-142461-0

Modern Semiconductor Devices for Integrated Circuits, First Edition introduces readers to the world of modern semiconductor devices with an emphasis on integrated circuit applications. KEY TOPICS: Electrons and Holes in Semiconductors; Motion and Recombination of Electrons and Holes; Device Fabrication Technology; PN and Metal-Semiconductor Junctions; MOS Capacitor; MOS Transistor; MOSFETs in ICs—Scaling, Leakage, and Other Topics; Bipolar Transistor. MARKET: Written by an experienced teacher, researcher, and expert in industry practices, this succinct and forward-looking text is appropriate for anyone interested in semiconductor devices for integrated circuits, and serves as a suitable reference text for practicing engineers.

From semiconductor fundamentals to semiconductor devices used in the telecommunications and computing industries, this 2005 book provides a solid grounding in the most important devices used in the hottest areas of electronic engineering. The book includes coverage of future approaches to computing hardware and RF power amplifiers, and explains how emerging trends and system demands of computing and telecommunications systems influence the choice, design and operation of semiconductors. Next, the field effect devices are described, including MODFETs and MOSFETs. Short channel effects and the challenges faced by continuing miniaturisation are then addressed. The rest of the book discusses the structure, behaviour, and operating requirements of semiconductor devices used in lightwave and wireless telecommunications systems. This is both an excellent senior/graduate text, and a valuable reference for engineers and researchers in the field.

A thoroughly updated third edition of a classic text, perfect for practical transistor design and in the classroom. It includes a variety of recent developments, reorganized chapters, and additional end-of-chapter homework exercises, making it ideal for senior undergraduate and graduate students taking advanced semiconductor devices courses.

During the last decade, there has been a great deal of interest in TFETs. To the best authors' knowledge, no book on TFETs currently exists. The proposed book provides readers with fundamental understanding of the TFETs. It explains the interesting characteristics of the TFETs, pointing to their strengths and weaknesses, and describes the novel techniques that can be employed to overcome these weaknesses and improve their characteristics. Different tradeoffs that can be made in designing TFETs have also been highlighted. Further, the book provides simulation example files of TFETs that could be run using a commercial device simulator.

Praise for CMOS: Circuit Design, Layout, and Simulation Revised Second Edition from the Technical Reviewers "A refreshing industrial flavor. Design concepts are presented as they are needed for 'just-in-time' learning. Simulating and designing circuits using SPICE is emphasized with literally hundreds of examples. Very few textbooks contain as much detail as this one. Highly recommended!" --Paul M. Furth, New Mexico State University "This book builds a solid knowledge of CMOS circuit design from the ground up. With coverage of process integration, layout, analog and digital models, noise mechanisms, memory circuits, references, amplifiers, PLLs/DLLs, dynamic circuits, and data converters, the text is an excellent reference for both experienced and novice designers alike." --Tyler J. Gomm, Design Engineer, Micron Technology, Inc. "The Second Edition builds upon the success of the first with new chapters that cover additional material such as oversampled converters and non-volatile memories. This is becoming the de facto standard textbook to have on every analog and mixed-signal designer's bookshelf." --Joe Walsh, Design Engineer, AMI Semiconductor CMOS circuits from design to implementation CMOS: Circuit Design, Layout, and Simulation, Revised Second Edition covers the practical design of both analog and digital integrated circuits, offering a vital, contemporary view of a wide range of analog/digital circuit blocks, the BSIM model, data converter architectures, and much more.

This edition takes a two-path approach to the topics: design techniques are developed for both long- and short-channel CMOS technologies and then compared. The results are multidimensional explanations that allow readers to gain deep insight into the design process. Features include: Updated materials to reflect CMOS technology's movement into nanometer sizes Discussions on phase- and delay-locked loops, mixed-signal circuits, data converters, and circuit noise More than 1,000 figures, 200 examples, and over 500 end-of-chapter problems In-depth coverage of both analog and digital circuit-level design techniques Real-world process parameters and design rules The book's Web site, CMOSedu.com, provides: solutions to the book's problems; additional homework problems without solutions; SPICE simulation examples using HSPICE, LTspice, and WinSpice; layout tools and examples for actually fabricating a chip; and videos to aid learning

Learn the basic properties and designs of modern VLSI devices, as well as the factors affecting performance, with this thoroughly updated second edition. The first edition has been widely adopted as a standard textbook in microelectronics in many major US universities and worldwide. The internationally renowned authors highlight the intricate interdependencies and subtle trade-offs between various practically important device parameters, and provide an in-depth discussion of device scaling and scaling limits of CMOS and bipolar devices. Equations and parameters provided are checked continuously against the reality of silicon data, making the book equally useful in practical transistor design and in the classroom. Every chapter has been updated to include the latest developments, such as MOSFET scale length theory, high-field transport model and SiGe-base bipolar devices.

This volume provides a timely description of the latest compact MOS transistor models for circuit simulation. The first generation BSIM3 and BSIM4 models that have dominated circuit simulation in the last decade are no longer capable of characterizing all the important features of modern sub-100nm MOS transistors. This book discusses the second generation MOS transistor models that are now in urgent demand and being brought into the initial phase of manufacturing applications. It considers how the models are to include the complete drift-diffusion theory using the surface potential variable in the MOS transistor channel in order to give one characterization equation.

This book covers the physics of semiconductors on an introductory level, assuming that the reader already has some knowledge of condensed matter physics. Crystal structure, band structure, carrier transport, phonons, scattering processes and optical properties are presented for typical semiconductors such as silicon, but III–V and II–VI compounds are also included. In view of the increasing importance of wide-gap semiconductors, the electronic and optical properties of these materials are dealt with too.

This book provides broad and comprehensive coverage of the entire EDA flow. EDA/VLSI practitioners and researchers in need of fluency in an "adjacent" field will find this an invaluable reference to the basic EDA concepts, principles, data structures, algorithms, and architectures for the design, verification, and test of VLSI circuits. Anyone who needs to learn the concepts, principles, data structures, algorithms, and architectures of the EDA flow will benefit from this book. Covers complete spectrum of the EDA flow, from ESL design modeling to logic/test synthesis, verification, physical design, and test - helps EDA newcomers to get "up-and-running" quickly Includes comprehensive coverage of EDA concepts, principles, data structures, algorithms, and architectures - helps all readers improve their VLSI design competence Contains latest advancements not yet available in other books, including Test compression, ESL design modeling, large-scale floorplanning, placement, routing, synthesis of clock and power/ground networks - helps readers to design/develop testable chips or products Includes industry best-practices wherever appropriate in most chapters - helps readers avoid costly mistakes

The transistor is the key enabler of modern electronics. Progress in transistor scaling has pushed channel lengths to the nanometer regime where traditional approaches to device physics are less and less suitable. These lectures describe a way of understanding MOSFETs and other transistors that is much more suitable than traditional approaches when the critical dimensions are measured in nanometers. It uses a novel, "bottom-up approach" that agrees with traditional methods when devices are large, but that also works for nano-devices. Surprisingly, the final result looks much like the traditional, textbook, transistor models, but the parameters in the equations have simple, clear interpretations at the nanoscale. The objective is to provide readers with an understanding of the essential physics of nanoscale transistors as well as some of the practical technological considerations and fundamental limits. This book is written in a way that is broadly accessible to students with only a very basic knowledge of semiconductor physics and electronic circuits. Complemented with online lecture by Prof Lundstrom: nanoHUB-U Nanoscale Transistor Contents: MOSFET Fundamentals: Overview The Transistor as a Black Box The MOSFET: A Barrier-Controlled Device MOSFET IV: Traditional Approach MOSFET IV: The Virtual Source Model MOS Electrostatics: Poisson Equation and the Depletion Approximation Gate Voltage and Surface Potential Mobile Charge: Bulk MOS Mobile Charge: Extremely Thin SOI 2D MOS Electrostatics The VS Model Revisited The Ballistic MOSFET: The Landauer Approach to Transport The Ballistic MOSFET The Ballistic Injection Velocity Connecting the Ballistic and VS Models Transmission Theory of the MOSFET: Carrier Scattering and Transmission Transmission Theory of the MOSFET Connecting the Transmission and VS Models VS Characterization of Transport in Nanotransistors Limits and Limitations Readership: Any student and professional with an undergraduate degree in the physical sciences or engineering.

This might be the first book that deals mostly with the 3D technology computer-aided design (TCAD) simulations of major state-of-the-art stress- and strain-engineered advanced semiconductor devices: MOSFETs, BJTs, HBTs, nonclassical MOS devices, finFETs, silicon-germanium hetero-FETs, solar cells, power devices, and memory devices. The book focuses on how to set up 3D TCAD simulation tools, from mask layout to process and device simulation, including design for manufacturing (DFM), and from device modeling to SPICE parameter extraction. The book also offers an innovative and new approach to teaching the fundamentals of semiconductor process and device design using advanced TCAD simulations of various semiconductor structures. The simulation examples chosen are from the most popular devices in use today and provide useful technology and device physics insights. To extend the role of TCAD in today's advanced technology era, process compact modeling and DFM issues have been included for design–technology interface generation. Unique in approach, this book provides an integrated view of silicon technology and beyond—with emphasis on TCAD simulations. It is the first book to provide a web-based online laboratory for semiconductor device characterization and SPICE parameter extraction. It describes not only the manufacturing practice associated with the technologies used but also the underlying scientific basis for those technologies. Written from an engineering standpoint, this book provides the process design and simulation background needed to understand new and future technology development, process modeling, and design of nanoscale transistors. The book also advances the understanding and knowledge of modern IC design via TCAD, improves the quality in micro- and nanoelectronics R&D, and supports the training of semiconductor specialists. It is intended as a textbook or reference for graduate students in the field of semiconductor fabrication and as a reference for engineers involved in VLSI technology development who have to solve device and process problems. CAD specialists will also find this book useful since it discusses the organization of the simulation system, in addition to presenting many case studies where the user applies TCAD tools in different situations.

The awaited revision of *Semiconductor Devices: Physics and Technology* offers more than 50% new or revised material that reflects a multitude of important discoveries and advances in device physics and integrated circuit processing. Offering a basic introduction to physical principles of modern semiconductor devices and their advanced fabrication technology, the third edition presents students with theoretical and practical aspects of every step in device characterizations and fabrication, with an emphasis on integrated circuits. Divided into three parts, this text covers the basic properties of semiconductor materials, emphasizing silicon and gallium arsenide; the physics and characteristics of semiconductor devices bipolar, unipolar special microwave and photonic devices; and the latest processing technologies, from crystal growth to lithographic pattern transfer.

A comprehensive introduction and up-to-date reference to SiC power semiconductor devices covering topics from material properties to applications. Based on a number of breakthroughs in SiC material science and fabrication technology in the 1980s and 1990s, the first SiC Schottky barrier diodes (SBDs) were released as commercial products in 2001. The SiC SBD market has grown significantly since that time, and SBDs are now used in a variety of power systems, particularly switch-mode power supplies and motor controls. SiC power MOSFETs entered commercial production in 2011, providing rugged, high-efficiency switches for high-frequency power systems. In this wide-ranging book, the authors draw on their considerable experience to present both an introduction to SiC materials, devices, and applications and an in-depth reference for scientists and engineers working in this fast-moving field. *Fundamentals of Silicon Carbide Technology* covers basic properties of SiC materials, processing technology, theory and analysis of practical devices, and an overview of the most important systems applications. Specifically included are: A complete discussion of SiC material properties, bulk crystal growth, epitaxial growth, device fabrication technology, and characterization techniques. Device physics and operating equations for Schottky diodes, pin diodes, JBS/MPS diodes, JFETs, MOSFETs, BJTs, IGBTs, and thyristors. A survey of power electronics applications, including switch-mode power supplies, motor drives, power converters for electric vehicles, and converters for renewable energy sources. Coverage of special applications, including microwave devices, high-temperature electronics, and rugged sensors. Fully illustrated throughout, the text is written by recognized experts with over 45 years of combined experience in SiC research and development. This book is intended for graduate students and researchers in crystal growth, material science, and semiconductor device technology. The book is also useful for design engineers, application engineers, and product managers in areas such as power supplies, converter and inverter design, electric vehicle technology, high-temperature electronics, sensors, and smart grid technology.

Unlike books currently on the market, this book attempts to satisfy two goals: combine circuits and electronics into a single, unified treatment, and establish a strong connection with the contemporary world of digital systems. It will introduce a new way of looking not only at the treatment of circuits, but also at the treatment of introductory coursework in engineering in general. Using the concept of "abstraction," the book attempts to form a bridge between the world of physics and the world of large computer systems. In particular, it attempts to unify electrical engineering and computer science as the art of creating and exploiting successive abstractions to manage the complexity of building useful electrical systems. Computer systems are simply one type of electrical systems. +Balances circuits theory with practical digital electronics applications. +Illustrates concepts with real devices. +Supports the popular circuits and electronics course on the MIT OpenCourseWare from which professionals worldwide study this new approach. +Written by two educators well known for their innovative teaching and research and their collaboration with industry. +Focuses on contemporary MOS technology.

The award-winning VLSI design guide is now fully updated to reflect the latest advances in chip design

To surmount the continuous scaling challenges of MOSFET devices, FinFETs have emerged as the real alternative for use as the next generation device for IC fabrication technology. The objective of this book is to provide the basic theory and operating principles of FinFET devices and technology, an overview of FinFET device architecture and manufacturing processes, and detailed formulation of FinFET electrostatic and dynamic device characteristics for IC design and manufacturing. Thus, this book caters to practicing engineers transitioning to FinFET technology and prepares the next generation of device engineers and academic experts on mainstream device technology at the nanometer-nodes.

*Formal Verification: An Essential Toolkit for Modern VLSI Design* presents practical approaches for design and validation, with hands-on advice to help working engineers integrate these techniques into their work. Formal Verification (FV) enables a designer to directly analyze and mathematically explore the quality or other aspects of a Register Transfer Level (RTL) design without using simulations. This can reduce time spent validating designs and more quickly reach a final design for manufacturing. Building on a basic knowledge of SystemVerilog, this book demystifies FV and presents the practical applications that are bringing it into mainstream design and validation processes at Intel and other companies. After reading this book, readers will be prepared to introduce FV in their organization and effectively deploy FV techniques to increase design and validation productivity. Learn formal verification algorithms to gain full coverage without exhaustive simulation Understand formal verification tools and how they differ from simulation tools Create instant test benches to gain insight into how models work and find initial bugs Learn from Intel insiders sharing their hard-won knowledge and solutions to complex design problems

*Fundamentals of Modern VLSI Devices* Cambridge University Press

Packed full of real circuits to build and test, *Hands-On Electronics* is a unique introduction to analog and digital electronics theory and practice. Ideal both as a college textbook and for self-study, the friendly style, clear illustrations and construction details included in the book encourage rapid and effective learning of analog and digital circuit design theory. All the major topics for a typical one semester course are covered including RC circuits, diodes, transistors, op-amps, oscillators, TTL logic, counters, D/A converters and more. There are also chapters explaining how to use the equipment needed for the examples (oscilloscope, multimeter and breadboard) together with pin-out diagrams and manufacturers' specifications for all the key components referred to in the book.

For Electrical Engineering and Computer Engineering courses that cover the design and technology of very large scale integrated (VLSI) circuits and systems. May also be used as a VLSI reference for professional VLSI design engineers, VLSI design managers, and VLSI CAD engineers. *Modern VLSI Design* provides a comprehensive "bottom-up" guide to the design of VLSI systems, from the physical design of circuits through system architecture with focus on the latest solution for system-on-chip (SOC) design. Because VLSI system designers face a variety of challenges that include high performance, interconnect delays, low power, low cost, and fast design turnaround time, successful designers must understand the entire design process. The Third Edition also provides a much more thorough discussion of hardware description languages, with introduction to both Verilog and VHDL. For that reason, this book presents the entire VLSI design process in a single volume.

Error-correcting codes are ubiquitous. They are adopted in almost every modern digital communication and storage system, such as wireless communications, optical communications, Flash memories, computer hard drives, sensor networks, and deep-space probing. New-generation and emerging applications demand codes with better error-correcting capability. On the other hand, the design and implementation of those high-gain error-correcting codes pose

many challenges. They usually involve complex mathematical computations, and mapping them directly to hardware often leads to very high complexity. VLSI Architectures for Modern Error-Correcting Codes serves as a bridge connecting advancements in coding theory to practical hardware implementations. Instead of focusing on circuit-level design techniques, the book highlights integrated algorithmic and architectural transformations that lead to great improvements on throughput, silicon area requirement, and/or power consumption in the hardware implementation. The goal of this book is to provide a comprehensive and systematic review of available techniques and architectures, so that they can be easily followed by system and hardware designers to develop en/decoder implementations that meet error-correcting performance and cost requirements. This book can be also used as a reference for graduate-level courses on VLSI design and error-correcting coding. Particular emphases are placed on hard- and soft-decision Reed-Solomon (RS) and Bose-Chaudhuri-Hocquenghem (BCH) codes, and binary and non-binary low-density parity-check (LDPC) codes. These codes are among the best candidates for modern and emerging applications due to their good error-correcting performance and lower implementation complexity compared to other codes. To help explain the computations and en/decoder architectures, many examples and case studies are included. More importantly, discussions are provided on the advantages and drawbacks of different implementation approaches and architectures.

This book deals mainly with physical device models which are developed from the carrier transport physics and device geometry considerations. The text concentrates on silicon and gallium arsenide devices and includes models of silicon bipolar junction transistors, junction field effect transistors (JFETs), MESFETs, silicon and GaAs MESFETs, transferred electron devices, pn junction diodes and Schottky varactor diodes. The modelling techniques of more recent devices such as the heterojunction bipolar transistors (HBT) and the high electron mobility transistors are discussed. This book contains details of models for both equilibrium and non-equilibrium transport conditions. The modelling Technique of Small-scale devices is discussed and techniques applicable to submicron-dimensioned devices are included. A section on modern quantum transport analysis techniques is included. Details of essential numerical schemes are given and a variety of device models are used to illustrate the application of these techniques in various fields.

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